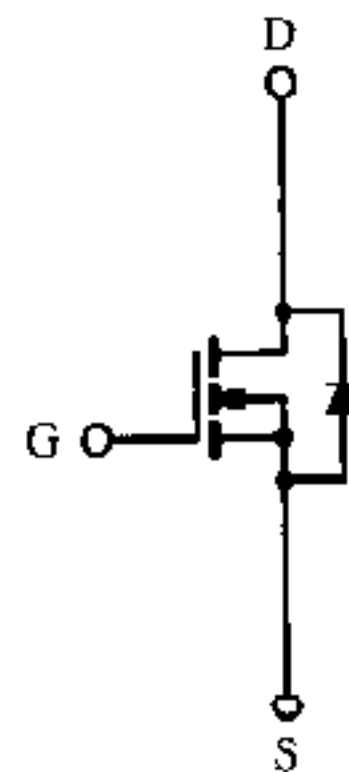
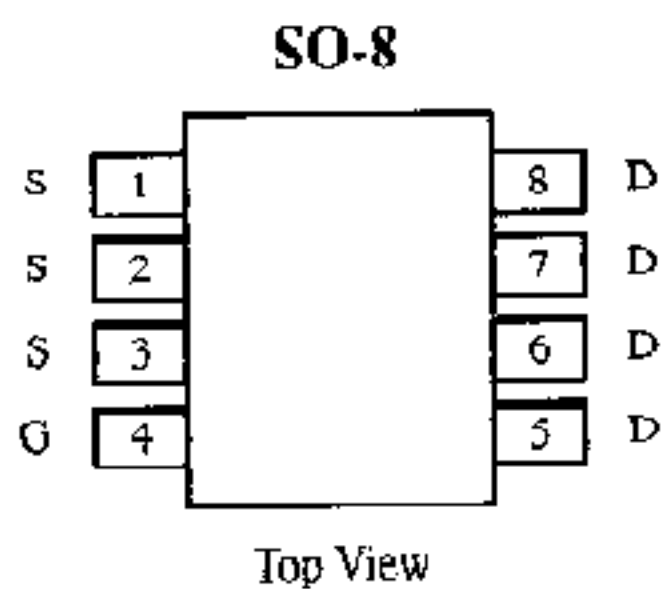


N-Channel Enhancement-Mode MOSFET

Product Summary

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0135 @ $V_{GS} = 10$ V	± 10
	0.020 @ $V_{GS} = 4.5$ V	± 8



N-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	± 10
		$T_A = 70^\circ\text{C}$	± 8
Pulsed Drain Current	I_{DM}	± 50	A
Continuous Source Current (Diode Conduction) ^a	I_S	2.3	A
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	2.5
		$T_A = 70^\circ\text{C}$	1.6
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	50	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Subsequent updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #1230. A SPICE Model data sheet is available for this product (FaxBack document #5126).